

1                   ABSTRACT OF THE DISCLOSURE

2                   The invention encompasses a method of removing at least some of  
3                   a material from a semiconductor substrate. A feed gas is fed through  
4                   an ozone generator to generate ozone. The feed gas comprises at least  
5                   99.999% O<sub>2</sub> (by volume). The ozone, or a fragment of the ozone, is  
6                   contacted with a material on a semiconductor substrate to remove at  
7                   least some of the material from the semiconductor substrate. The  
8                   invention also encompasses another method of removing at least some of  
9                   a material from a semiconductor substrate. A mixture of ozone and  
10                  organic solvent vapors is formed in a reaction chamber. At least some  
11                  of the ozone and solvent vapors are contacted with a material on a  
12                  semiconductor substrate to remove at least some of the material from  
13                  the semiconductor substrate.

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